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Embedded - System On Chip (SoC): The Heart of Modern Embedded Systems

Embedded - System On Chip (SoC) refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

What are Embedded - System On Chip (SoC)?

System On Chip (SoC) integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

Details	
Product Status	Active
Architecture	MCU, FPGA
Core Processor	Dual ARM® Cortex®-A53 MPCore™ with CoreSight™, Dual ARM®Cortex™-R5 with CoreSight™
Flash Size	-
RAM Size	256KB
Peripherals	DMA, WDT
Connectivity	CANbus, EBI/EMI, Ethernet, I ² C, MMC/SD/SDIO, SPI, UART/USART, USB OTG
Speed	533MHz, 1.3GHz
Primary Attributes	Zynq®UltraScale+™ FPGA, 192K+ Logic Cells
Operating Temperature	0°C ~ 100°C (TJ)
Package / Case	900-BBGA, FCBGA
Supplier Device Package	900-FCBGA (31x31)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xczu4cg-2fbvb900e

Recommended Operating Conditions

 Table 2: Recommended Operating Conditions⁽¹⁾⁽²⁾

Symbol	Description	Min	Typ	Max	Units
Processor System					
V _{CC_PSINTFP} ⁽³⁾	PS full-power domain supply voltage.	0.808	0.850	0.892	V
	For -1LI and -2LE (V _{CCINT} = 0.72V) devices: PS full-power domain supply voltage.	0.808	0.850	0.892	V
	For -3E devices: PS full-power domain supply voltage.	0.873	0.900	0.927	V
V _{CC_PSINTLP}	PS low-power domain supply voltage.	0.808	0.850	0.892	V
	For -1LI and -2LE (V _{CCINT} = 0.72V) devices: PS low-power domain supply voltage.	0.808	0.850	0.892	V
	For -3E devices: PS low-power domain supply voltage.	0.873	0.900	0.927	V
V _{CC_PSAUX}	PS auxiliary supply voltage.	1.710	1.800	1.890	V
V _{CC_PSINTFP_DDR} ⁽³⁾	PS DDR controller and PHY supply voltage.	0.808	0.850	0.892	V
	For -1LI and -2LE (V _{CCINT} = 0.72V) devices: PS DDR controller and PHY supply voltage.	0.808	0.850	0.892	V
	For -3E devices: PS DDR controller and PHY supply voltage.	0.873	0.900	0.927	V
V _{CC_PSADC}	PS SYSMON ADC supply voltage relative to GND_PSADC.	1.710	1.800	1.890	V
V _{CC_PSPLL}	PS PLL supply voltage.	1.164	1.200	1.236	V
V _{PS_MGTRAVCC}	PS-GTR supply voltage.	0.825	0.850	0.875	V
V _{PS_MGTRAVTT}	PS-GTR termination voltage.	1.746	1.800	1.854	V
V _{CCO_PSDDR} ⁽⁴⁾	PS DDR I/O supply voltage.	1.06	–	1.575	V
V _{CC_PSDDR_PLL}	PS DDR PLL supply voltage.	1.710	1.800	1.890	V
V _{CCO_PSIO} ⁽⁵⁾	PS I/O supply.	1.710	–	3.465	V
V _{PSIN}	PS I/O input voltage.	–0.200	–	V _{CCO_PSIO} + 0.200	V
	PS DDR I/O input voltage.	–0.200	–	V _{CCO_PSDDR} + 0.200	
V _{CC_PSBATT} ⁽⁶⁾	PS battery-backed RAM and battery-backed real-time clock (RTC) supply voltage.	1.200	–	1.500	V
Programmable Logic					
V _{CCINT}	PL internal supply voltage.	0.825	0.850	0.876	V
	For -1LI and -2LE (V _{CCINT} = 0.72V) devices: PL internal supply voltage.	0.698	0.720	0.742	V
	For -3E devices: PL internal supply voltage.	0.873	0.900	0.927	V
V _{CCINT_IO} ⁽⁷⁾	PL internal supply voltage for the I/O banks.	0.825	0.850	0.876	V
	For -1LI and -2LE (V _{CCINT} = 0.72V) devices: PL internal supply voltage for the I/O banks.	0.825	0.850	0.876	V
	For -3E devices: PL internal supply voltage for the I/O banks.	0.873	0.900	0.927	V
V _{CCBRAM}	Block RAM supply voltage.	0.825	0.850	0.876	V
	For -3E devices: block RAM supply voltage.	0.873	0.900	0.927	V
V _{CCAUX}	Auxiliary supply voltage.	1.746	1.800	1.854	V

Table 4: DC Characteristics Over Recommended Operating Conditions (Cont'd)

Symbol	Description	Min	Typ ⁽¹⁾	Max	Units
I _{CC_PSBATT} ⁽⁴⁾⁽⁵⁾	Battery supply current at V _{CC_PSBATT} = 1.50V, RTC enabled.	–	–	3650	nA
	Battery supply current at V _{CC_PSBATT} = 1.50V, RTC disabled.	–	–	650	nA
	Battery supply current at V _{CC_PSBATT} = 1.20V, RTC enabled.	–	–	3150	nA
	Battery supply current at V _{CC_PSBATT} = 1.20V, RTC disabled.	–	–	150	nA
I _{PSFS} ⁽⁶⁾	PS V _{CC_PSAUX} additional supply current during eFUSE programming.	–	–	115	mA
<i>Calibrated programmable on-die termination (DCI) in HP I/O banks⁽⁸⁾ (measured per JEDEC specification)</i>					
R ⁽⁹⁾	Thevenin equivalent resistance of programmable input termination to V _{CC0} /2 where ODT = RTT_40.	–10% ⁽⁷⁾	40	+10% ⁽⁷⁾	Ω
	Thevenin equivalent resistance of programmable input termination to V _{CC0} /2 where ODT = RTT_48.	–10% ⁽⁷⁾	48	+10% ⁽⁷⁾	Ω
	Thevenin equivalent resistance of programmable input termination to V _{CC0} /2 where ODT = RTT_60.	–10% ⁽⁷⁾	60	+10% ⁽⁷⁾	Ω
	Programmable input termination to V _{CC0} where ODT = RTT_40.	–10% ⁽⁷⁾	40	+10% ⁽⁷⁾	Ω
	Programmable input termination to V _{CC0} where ODT = RTT_48.	–10% ⁽⁷⁾	48	+10% ⁽⁷⁾	Ω
	Programmable input termination to V _{CC0} where ODT = RTT_60.	–10% ⁽⁷⁾	60	+10% ⁽⁷⁾	Ω
	Programmable input termination to V _{CC0} where ODT = RTT_120.	–10% ⁽⁷⁾	120	+10% ⁽⁷⁾	Ω
	Programmable input termination to V _{CC0} where ODT = RTT_240.	–10% ⁽⁷⁾	240	+10% ⁽⁷⁾	Ω
<i>Uncalibrated programmable on-die termination in HP I/Os banks (measured per JEDEC specification)</i>					
R ⁽⁹⁾	Thevenin equivalent resistance of programmable input termination to V _{CC0} /2 where ODT = RTT_40.	–50%	40	+50%	Ω
	Thevenin equivalent resistance of programmable input termination to V _{CC0} /2 where ODT = RTT_48.	–50%	48	+50%	Ω
	Thevenin equivalent resistance of programmable input termination to V _{CC0} /2 where ODT = RTT_60.	–50%	60	+50%	Ω
	Programmable input termination to V _{CC0} where ODT = RTT_40.	–50%	40	+50%	Ω
	Programmable input termination to V _{CC0} where ODT = RTT_48.	–50%	48	+50%	Ω
	Programmable input termination to V _{CC0} where ODT = RTT_60.	–50%	60	+50%	Ω
	Programmable input termination to V _{CC0} where ODT = RTT_120.	–50%	120	+50%	Ω
	Programmable input termination to V _{CC0} where ODT = RTT_240.	–50%	240	+50%	Ω
<i>Uncalibrated programmable on-die termination in HD I/O banks (measured per JEDEC specification)</i>					
R ⁽⁹⁾	Thevenin equivalent resistance of programmable input termination to V _{CC0} /2 where ODT = RTT_48.	–50%	48	+50%	Ω
Internal V _{REF}	50% V _{CC0}	V _{CC0} × 0.49	V _{CC0} × 0.50	V _{CC0} × 0.51	v
	70% V _{CC0}	V _{CC0} × 0.69	V _{CC0} × 0.70	V _{CC0} × 0.71	v

Table 19: Complementary Differential SelectIO DC Input and Output Levels for HP I/O Banks⁽¹⁾

I/O Standard	V _{ICM} (V) ⁽²⁾			V _{ID} (V) ⁽³⁾		V _{OL} (V) ⁽⁴⁾	V _{OH} (V) ⁽⁵⁾	I _{OL}	I _{OH}
	Min	Typ	Max	Min	Max	Max	Min	mA	mA
DIFF_HSTL_I	0.680	V _{CCO} /2	(V _{CCO} /2) + 0.150	0.100	–	0.400	V _{CCO} – 0.400	5.8	–5.8
DIFF_HSTL_I_12	0.400 x V _{CCO}	V _{CCO} /2	0.600 x V _{CCO}	0.100	–	0.250 x V _{CCO}	0.750 x V _{CCO}	4.1	–4.1
DIFF_HSTL_I_18	(V _{CCO} /2) – 0.175	V _{CCO} /2	(V _{CCO} /2) + 0.175	0.100	–	0.400	V _{CCO} – 0.400	6.2	–6.2
DIFF_HSUL_12	(V _{CCO} /2) – 0.120	V _{CCO} /2	(V _{CCO} /2) + 0.120	0.100	–	20% V _{CCO}	80% V _{CCO}	0.1	–0.1
DIFF_SSTL12	(V _{CCO} /2) – 0.150	V _{CCO} /2	(V _{CCO} /2) + 0.150	0.100	–	(V _{CCO} /2) – 0.150	(V _{CCO} /2) + 0.150	8.0	–8.0
DIFF_SSTL135	(V _{CCO} /2) – 0.150	V _{CCO} /2	(V _{CCO} /2) + 0.150	0.100	–	(V _{CCO} /2) – 0.150	(V _{CCO} /2) + 0.150	9.0	–9.0
DIFF_SSTL15	(V _{CCO} /2) – 0.175	V _{CCO} /2	(V _{CCO} /2) + 0.175	0.100	–	(V _{CCO} /2) – 0.175	(V _{CCO} /2) + 0.175	10.0	–10.0
DIFF_SSTL18_I	(V _{CCO} /2) – 0.175	V _{CCO} /2	(V _{CCO} /2) + 0.175	0.100	–	(V _{CCO} /2) – 0.470	(V _{CCO} /2) + 0.470	7.0	–7.0

Notes:

1. DIFF_POD10 and DIFF_POD12 HP I/O bank specifications are shown in Table 20, Table 21, and Table 22.
2. V_{ICM} is the input common mode voltage.
3. V_{ID} is the input differential voltage.
4. V_{OL} is the single-ended low-output voltage.
5. V_{OH} is the single-ended high-output voltage.

Table 20: DC Input Levels for Differential POD10 and POD12 I/O Standards⁽¹⁾⁽²⁾

I/O Standard	V _{ICM} (V)			V _{ID} (V)	
	Min	Typ	Max	Min	Max
DIFF_POD10	0.63	0.70	0.77	0.14	–
DIFF_POD12	0.76	0.84	0.92	0.16	–

Notes:

1. Tested according to relevant specifications.
2. Standards specified using the default I/O standard configuration. For details, see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).

Table 21: DC Output Levels for Single-ended and Differential POD10 and POD12 Standards⁽¹⁾⁽²⁾

Symbol	Description	V _{OUT}	Min	Typ	Max	Units
R _{OL}	Pull-down resistance.	V _{OM_DC} (as described in Table 22)	36	40	44	Ω
R _{OH}	Pull-up resistance.	V _{OM_DC} (as described in Table 22)	36	40	44	Ω

Notes:

1. Tested according to relevant specifications.
2. Standards specified using the default I/O standard configuration. For details, see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).

Table 22: Table 21 Definitions for DC Output Levels for POD Standards

Symbol	Description	All Speed Grades	Units
V _{OM_DC}	DC output Mid measurement level (for IV curve linearity).	0.8 x V _{CCO}	V

LVDS DC Specifications (LVDS_25)

The LVDS_25 standard is available in the HD I/O banks. See the *UltraScale Architecture SelectIO Resources User Guide* ([UG571](#)) for more information.

Table 23: LVDS_25 DC Specifications

Symbol	DC Parameter	Min	Typ	Max	Units
$V_{CCO}^{(1)}$	Supply voltage.	2.375	2.500	2.625	V
V_{IDIFF}	Differential input voltage: ($\overline{Q} - Q$), $\overline{Q} = \text{High}$ ($Q - \overline{Q}$), $Q = \text{High}$	100	350	600 ⁽²⁾	mV
V_{ICM}	Input common-mode voltage.	0.300	1.200	1.425	V

Notes:

1. LVDS_25 in HD I/O banks supports inputs only. LVDS_25 inputs without internal termination have no V_{CCO} requirements. Any V_{CCO} can be chosen as long as the input voltage levels do not violate the *Recommended Operating Condition* (Table 2) specification for the V_{IN} I/O pin voltage.
2. Maximum V_{IDIFF} value is specified for the maximum V_{ICM} specification. With a lower V_{ICM} , a higher V_{IDIFF} is tolerated only when the recommended operating conditions and overshoot/undershoot V_{IN} specifications are maintained.

LVDS DC Specifications (LVDS)

The LVDS standard is available in the HP I/O banks. See the *UltraScale Architecture SelectIO Resources User Guide* ([UG571](#)) for more information.

Table 24: LVDS DC Specifications

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
$V_{CCO}^{(1)}$	Supply voltage.		1.710	1.800	1.890	V
$V_{ODIFF}^{(2)}$	Differential output voltage: ($\overline{Q} - Q$), $\overline{Q} = \text{High}$ ($Q - \overline{Q}$), $Q = \text{High}$	$R_T = 100\Omega$ across Q and \overline{Q} signals	247	350	454	mV
$V_{OCM}^{(2)}$	Output common-mode voltage.	$R_T = 100\Omega$ across Q and \overline{Q} signals	1.000	1.250	1.425	V
$V_{IDIFF}^{(3)}$	Differential input voltage: ($\overline{Q} - Q$), $\overline{Q} = \text{High}$ ($Q - \overline{Q}$), $Q = \text{High}$		100	350	600 ⁽³⁾	mV
$V_{ICM_DC}^{(4)}$	Input common-mode voltage (DC coupling).		0.300	1.200	1.425	V
$V_{ICM_AC}^{(5)}$	Input common-mode voltage (AC coupling).		0.600	–	1.100	V

Notes:

1. In HP I/O banks, when LVDS is used with input-only functionality, it can be placed in a bank where the V_{CCO} levels are different from the specified level only if internal differential termination is not used. In this scenario, V_{CCO} must be chosen to ensure the input pin voltage levels do not violate the *Recommended Operating Condition* (Table 2) specification for the V_{IN} I/O pin voltage.
2. V_{OCM} and V_{ODIFF} values are for $LVDS_PRE_EMPHASIS = \text{FALSE}$.
3. Maximum V_{IDIFF} value is specified for the maximum V_{ICM} specification. With a lower V_{ICM} , a higher V_{IDIFF} is tolerated only when the recommended operating conditions and overshoot/undershoot V_{IN} specifications are maintained.
4. Input common mode voltage for DC coupled configurations. $EQUALIZATION = \text{EQ_NONE}$ (Default).
5. External input common mode voltage specification for AC coupled configurations. $EQUALIZATION = \text{EQ_LEVEL0}$, EQ_LEVEL1 , EQ_LEVEL2 , EQ_LEVEL3 , EQ_LEVEL4 .

Table 26: Speed Grade Designations by Device (Cont'd)

Device	Speed Grade, Temperature Ranges, and V_{CCINT} Operating Voltages		
	Advance	Preliminary	Production
XCZU11EG	-3E ($V_{CCINT} = 0.90V$), -2E ($V_{CCINT} = 0.85V$) -2I ($V_{CCINT} = 0.85V$), -2LE ($V_{CCINT} = 0.85V$) -1E ($V_{CCINT} = 0.85V$), -1I ($V_{CCINT} = 0.85V$) -1LI ($V_{CCINT} = 0.85V$) -2LE ($V_{CCINT} = 0.72V$), -1LI ($V_{CCINT} = 0.72V$)		
XCZU15EG	-3E ($V_{CCINT} = 0.90V$), -2E ($V_{CCINT} = 0.85V$) -2I ($V_{CCINT} = 0.85V$), -2LE ($V_{CCINT} = 0.85V$) -1E ($V_{CCINT} = 0.85V$), -1I ($V_{CCINT} = 0.85V$) -1LI ($V_{CCINT} = 0.85V$) -2LE ($V_{CCINT} = 0.72V$), -1LI ($V_{CCINT} = 0.72V$)		
XCZU17EG	-3E ($V_{CCINT} = 0.90V$), -2E ($V_{CCINT} = 0.85V$) -2I ($V_{CCINT} = 0.85V$), -2LE ($V_{CCINT} = 0.85V$) -1E ($V_{CCINT} = 0.85V$), -1I ($V_{CCINT} = 0.85V$) -1LI ($V_{CCINT} = 0.85V$) -2LE ($V_{CCINT} = 0.72V$), -1LI ($V_{CCINT} = 0.72V$)		
XCZU19EG	-3E ($V_{CCINT} = 0.90V$), -2E ($V_{CCINT} = 0.85V$) -2I ($V_{CCINT} = 0.85V$), -2LE ($V_{CCINT} = 0.85V$) -1E ($V_{CCINT} = 0.85V$), -1I ($V_{CCINT} = 0.85V$) -1LI ($V_{CCINT} = 0.85V$) -2LE ($V_{CCINT} = 0.72V$), -1LI ($V_{CCINT} = 0.72V$)		

Notes:

1. The lowest power -1L and -2L devices, where $V_{CCINT} = 0.72V$, are listed in the Vivado Design Suite as -1LV and -2LV respectively.

PS Switching Characteristics

PS Clocks

Table 34: PS Reference Clock Requirements⁽¹⁾

Symbol	Description	Min	Typ	Max	Units
T _{RMSJPSCLK}	PS_REF_CLK input RMS clock jitter.	–	–	3	ps
T _{PJPSCLK}	PS_REF_CLK input period jitter (peak-to-peak). Number of clock cycles = 10,000	–	–	50	ps
T _{DCPSCLK}	PS_REF_CLK duty cycle.	45	–	55	%
T _{RFPSCLK}	PS_REF_CLK rise time (20%–80%) and fall time (80%–20%).	–	–	2.22	ns
F _{PSCLK}	PS_REF_CLK frequency.	27	–	60	MHz

Notes:

1. The values in this table are applicable to alternative PS reference clock inputs ALT_REF_CLK, AUX_REF_CLK, and VIDEO_CLK.

Table 35: PS RTC Crystal Requirements⁽¹⁾

Symbol	Description	Min	Typ	Max	Units
F _{XTAL}	Parallel resonance crystal frequency.	–	32.8	–	KHz
T _{FTXTAL}	Frequency tolerance.	–20	–	20	ppm
C _{XTAL}	Load capacitance for crystal parallel resonance.	–	12.5	–	pF
R _{ESR}	Crystal ESR (16.8 and 19.2 MHz).	–	70	–	KΩ
C _{SHUNT}	Crystal shunt capacitance.	–	1.4	–	pF

Notes:

1. Required board components: Feedback resistor = 4.7 MΩ, PCB and pad capacitance = 1.5 pF, C₁ and C₂ capacitance = 21 pF.

Table 36: PS PLL Switching Characteristics

Symbol	Description	Speed Grade			Units
		-3	-2	-1	
F _{LOCKPSPLL}	PLL maximum lock time.	100	100	100	μs
F _{PSPLLMAX}	PLL maximum output frequency.	1600	1600	1600	MHz
F _{PSPLLMIN}	PLL minimum output frequency.	750	750	750	MHz
F _{PSPLLVCOMAX}	PLL maximum VCO frequency.	3000	3000	3000	MHz
F _{PSPLLVCOMIN}	PLL minimum VCO frequency.	1500	1500	1500	MHz

Table 37: PS Reset Assertion Timing Requirements

Symbol	Description	Min	Typ	Max	Units
T _{PSPOR}	Required PS_POR_B assertion time. (1)	10	–	–	μs
T _{PSRST}	Required PS_SRST_B assertion time.	3	–	–	PS_REF_CLK Clock Cycles

Notes:

1. PS_POR_B must be asserted Low at power-up and continue to be asserted for a duration of T_{PSPOR} after all the PS supply voltages reach minimum levels. PS_POR_B must be asserted Low for the duration of T_{POR} when the PS and PL power-up at the same time and the application uses both the PS and PL after power-up.

Table 38: PS Clocks Switching Characteristics

Symbol	Description	Speed Grade			Units
		-3	-2	-1	
F _{TOPSW_MAINMAX}	TOPSW_MAIN maximum frequency.	600	533	533	MHz
F _{TOPSW_LSBUSMAX}	TOPSW_LSBUS maximum frequency.	100	100	100	MHz
F _{GDMAMAX}	FPD-DMA maximum frequency.	600	600	600	MHz
F _{DPMAMAX}	DisplayPort DMA maximum frequency.	600	600	600	MHz
F _{LPD_SWITCH_CTRLMAX}	LPD_SWITCH_CTRL maximum frequency.	600	500	500	MHz
F _{LPD_LSBUS_CTRLMAX}	LPD_LSBUS_CTRL maximum frequency.	100	100	100	MHz
F _{ADMAMAX}	LPD-DMA maximum frequency.	600	500	500	MHz
F _{APLL_TO_LPDMAX}	APLL_TO_LPD maximum frequency.	533	533	533	MHz
F _{DPDLL_TO_LPDMAX}	DPDLL_TO_LPD maximum frequency.	533	533	533	MHz
F _{VPDLL_TO_LPDMAX}	VPDLL_TO_LPD maximum frequency.	533	533	533	MHz
F _{IOPLL_TO_LPDMAX}	IOPLL_TO_LPD maximum frequency.	533	533	533	MHz
F _{RPLL_TO_FPDMAX}	RPLL_TO_FPD maximum frequency.	533	533	533	MHz

PS Interface Specifications

PS Quad-SPI Controller Interface

Table 41: Generic Quad-SPI Interface⁽¹⁾

Symbol	Description	Load Conditions ⁽²⁾	Min	Max	Units
Quad-SPI device clock frequency operating at 150 MHz. Loopback enabled. LVCMOS 1.8V I/O standard.					
T _{DCQSPICLK1}	Quad-SPI clock duty cycle.	15 pF	45	55	%
T _{QSPISSSCLK1}	Slave select asserted to next clock edge.	15 pF	5.0	–	ns
T _{QSPISCLKSS1}	Clock edge to slave select deasserted.	15 pF	5.0	–	ns
T _{QSPICKO1}	Clock to output delay, all outputs.	15 pF	2.9	4.5	ns
T _{QSPIDCK1}	Setup time, all inputs.	15 pF	0.9	–	ns
T _{QSPICKD1}	Hold time, all inputs.	15 pF	1.0	–	ns
F _{QSPICLK1}	Quad-SPI device clock frequency.	15 pF	–	150	MHz
F _{QSPIREFCLK1}	Quad-SPI reference clock frequency.	15 pF	–	300	MHz
Quad-SPI device clock frequency operating at 100 MHz. Loopback enabled. LVCMOS 1.8V I/O standard.					
T _{DCQSPICLK2}	Quad-SPI clock duty cycle.	15 pF	45	55	%
		30 pF	45	55	%
T _{QSPISSSCLK2}	Slave select asserted to next clock edge.	15 pF	5.0	–	ns
		30 pF	5.0	–	ns
T _{QSPISCLKSS2}	Clock edge to slave select deasserted.	15 pF	5.0	–	ns
		30 pF	5.0	–	ns
T _{QSPICKO2}	Clock to output delay, all outputs.	15 pF	3.2	7.4	ns
		30 pF	3.2	7.4	ns
T _{QSPIDCK2}	Setup time, all inputs.	15 pF	2.3	–	ns
		30 pF	2.3	–	ns
T _{QSPICKD2}	Hold time, all inputs.	15 pF	0.0	–	ns
		30 pF	0.0	–	ns
F _{QSPICLK2}	Quad-SPI device clock frequency.	15 pF	–	100	MHz
		30 pF	–	100	MHz
F _{QSPIREFCLK2}	Quad-SPI reference clock frequency.	15 pF	–	200	MHz
		30 pF	–	200	MHz

Notes:

1. The test conditions are configured for the generic Quad-SPI interface at 150/100 MHz with a 12 mA drive strength and fast slew rate.
2. 30 pF loads are for dual-parallel stacked or stacked modes.

PS I2C Controller Interface

Table 47: I2C Interface⁽¹⁾

Symbol	Description	Min	Max	Units
I2C Fast-mode Interface				
$T_{I2CFCKL}$	SCL Low time.	1.3	–	μ s
$T_{I2CFCKH}$	SCL High time.	0.6	–	μ s
$T_{I2CFCKO}$	SDA clock to out delay.	–	900	ns
$T_{I2CFDCK}$	SDA input setup time.	100	–	ns
$F_{I2CFCLK}$	SCL clock frequency.	–	400	KHz
I2C Standard-mode Interface				
$T_{I2CSCKL}$	SCL Low time.	4.7	–	μ s
$T_{I2CSCKH}$	SCL High time.	4.0	–	μ s
$T_{I2CSCKO}$	SDA clock to out delay.	–	3450	ns
$T_{I2CSDCK}$	SDA input setup time.	250	–	ns
$F_{I2CSCLK}$	SCL clock frequency.	–	100	KHz

Notes:

1. The test conditions are configured to the LVCMOS 3.3V I/O standard with a 12 mA drive strength, fast slew rate, and a 15 pF load.

PS Triple-timer Counter Interface

Table 54: Triple-timer Counter Interface

Symbol	Description	Min	Max	Units
$T_{PWTTCOCLK}$	Triple-timer counter output clock pulse width.	60.4	–	ns
$F_{TTCOCLK}$	Triple-timer counter output clock frequency.	–	16.5	MHz
$T_{TTCICLKL}$	Triple-timer counter input clock high pulse width.	$1.5 \times 1/F_{LPD_LSBUS_CTRLMAX}$	–	ns
$T_{TTCICLKH}$	Triple-timer counter input clock low pulse width.	$1.5 \times 1/F_{LPD_LSBUS_CTRLMAX}$	–	ns
$F_{TTCICLK}$	Triple-timer counter input clock frequency.	–	$F_{LPD_LSBUS_CTRLMAX}/3$	MHz

Notes:

1. All timing values assume an ideal external input clock. Your actual timing budget must account for additional external clock jitter.

PS Watchdog Timer Interface

Table 55: Watchdog Timer Interface

Symbol	Description	Min	Max	Units
F_{WDTCLK}	Watchdog timer input clock frequency.	–	100	MHz

Programmable Logic (PL) Switching Characteristics

Table 75 (high-density IOB (HD)) and Table 76 (high-performance IOB (HP)) summarizes the values of standard-specific data input delay adjustments, output delays terminating at pads (based on standard) and 3-state delays.

- $T_{INBUF_DELAY_PAD_I}$ is the delay from IOB pad through the input buffer to the I-pin of an IOB pad. The delay varies depending on the capability of the SelectIO input buffer.
- $T_{OUTBUF_DELAY_O_PAD}$ is the delay from the O pin to the IOB pad through the output buffer of an IOB pad. The delay varies depending on the capability of the SelectIO output buffer.
- $T_{OUTBUF_DELAY_TD_PAD}$ is the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is disabled. The delay varies depending on the SelectIO capability of the output buffer. In HP I/O banks, the internal DCI termination turn-on time is always faster than $T_{OUTBUF_DELAY_TD_PAD}$ when the DCITERMDISABLE pin is used. In HD I/O banks, the on-die termination turn-on time is always faster than $T_{OUTBUF_DELAY_TD_PAD}$ when the INTERMDISABLE pin is used.

IOB High Density (HD) Switching Characteristics

Table 75: IOB High Density (HD) Switching Characteristics

I/O Standards	$T_{INBUF_DELAY_PAD_I}$					$T_{OUTBUF_DELAY_O_PAD}$					$T_{OUTBUF_DELAY_TD_PAD}$					Units
	0.90V		0.85V		0.72V	0.90V		0.85V		0.72V	0.90V		0.85V		0.72V	
	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	
DIFF_HSTL_I_18_F	0.978	0.978	1.058	0.978	1.058	1.574	1.574	1.718	1.574	1.718	1.160	1.160	1.271	1.160	1.271	ns
DIFF_HSTL_I_18_S	0.978	0.978	1.058	0.978	1.058	1.805	1.805	1.950	1.805	1.950	1.748	1.748	1.867	1.748	1.867	ns
DIFF_HSTL_I_F	0.978	0.978	1.058	0.978	1.058	1.611	1.611	1.762	1.611	1.762	1.313	1.313	1.417	1.313	1.417	ns
DIFF_HSTL_I_S	0.978	0.978	1.058	0.978	1.058	1.798	1.798	1.913	1.798	1.913	1.630	1.630	1.780	1.630	1.780	ns
DIFF_HSUL_12_F	0.911	0.911	0.977	0.911	0.977	1.573	1.573	1.703	1.573	1.703	1.222	1.222	1.335	1.222	1.335	ns
DIFF_HSUL_12_S	0.911	0.911	0.977	0.911	0.977	1.711	1.711	1.864	1.711	1.864	1.536	1.536	1.665	1.536	1.665	ns
DIFF_SSTL12_F	0.906	0.906	0.977	0.906	0.977	1.643	1.643	1.792	1.643	1.792	1.285	1.285	1.423	1.285	1.423	ns
DIFF_SSTL12_S	0.906	0.906	0.977	0.906	0.977	1.784	1.784	1.948	1.784	1.948	1.567	1.567	1.706	1.567	1.706	ns
DIFF_SSTL135_F	0.927	0.927	0.995	0.927	0.995	1.625	1.625	1.765	1.625	1.765	1.341	1.341	1.458	1.341	1.458	ns
DIFF_SSTL135_II_F	0.927	0.927	0.995	0.927	0.995	1.623	1.623	1.770	1.623	1.770	1.325	1.325	1.470	1.325	1.470	ns
DIFF_SSTL135_II_S	0.927	0.927	0.995	0.927	0.995	1.768	1.768	1.916	1.768	1.916	1.722	1.722	1.911	1.722	1.911	ns
DIFF_SSTL135_S	0.927	0.927	0.995	0.927	0.995	1.869	1.869	2.025	1.869	2.025	1.814	1.814	1.976	1.814	1.976	ns
DIFF_SSTL15_F	0.928	0.928	1.020	0.928	1.020	1.628	1.628	1.771	1.628	1.771	1.374	1.374	1.483	1.374	1.483	ns
DIFF_SSTL15_II_F	0.928	0.928	1.020	0.928	1.020	1.622	1.622	1.778	1.622	1.778	1.356	1.356	1.442	1.356	1.442	ns
DIFF_SSTL15_II_S	0.928	0.928	1.020	0.928	1.020	1.821	1.821	1.987	1.821	1.987	1.895	1.895	2.047	1.895	2.047	ns
DIFF_SSTL15_S	0.928	0.928	1.020	0.928	1.020	1.824	1.824	1.977	1.824	1.977	1.743	1.743	1.907	1.743	1.907	ns
DIFF_SSTL18_II_F	0.961	0.961	1.038	0.961	1.038	1.729	1.729	1.880	1.729	1.880	1.377	1.377	1.492	1.377	1.492	ns
DIFF_SSTL18_II_S	0.961	0.961	1.038	0.961	1.038	1.796	1.796	1.965	1.796	1.965	1.616	1.616	1.800	1.616	1.800	ns
DIFF_SSTL18_I_F	0.961	0.961	1.038	0.961	1.038	1.609	1.609	1.755	1.609	1.755	1.220	1.220	1.313	1.220	1.313	ns
DIFF_SSTL18_I_S	0.961	0.961	1.038	0.961	1.038	1.786	1.786	1.942	1.786	1.942	1.677	1.677	1.836	1.677	1.836	ns
HSTL_I_18_F	0.947	0.947	1.021	0.947	1.021	1.574	1.574	1.718	1.574	1.718	1.160	1.160	1.271	1.160	1.271	ns
HSTL_I_18_S	0.947	0.947	1.021	0.947	1.021	1.805	1.805	1.950	1.805	1.950	1.748	1.748	1.867	1.748	1.867	ns

IOB High Performance (HP) Switching Characteristics

Table 76: IOB High Performance (HP) Switching Characteristics

I/O Standards	T _{INBUF_DELAY_PAD_I}					T _{OUTBUF_DELAY_O_PAD}					T _{OUTBUF_DELAY_TD_PAD}					Units
	0.90V		0.85V		0.72V	0.90V		0.85V		0.72V	0.90V		0.85V		0.72V	
	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	
DIFF_HSTL_I_12_F	0.394	0.394	0.402	0.394	0.402	0.423	0.423	0.443	0.423	0.443	0.553	0.553	0.582	0.553	0.582	ns
DIFF_HSTL_I_12_M	0.394	0.394	0.402	0.394	0.402	0.552	0.552	0.583	0.552	0.583	0.641	0.641	0.679	0.641	0.679	ns
DIFF_HSTL_I_12_S	0.394	0.394	0.402	0.394	0.402	0.752	0.752	0.800	0.752	0.800	0.813	0.813	0.868	0.813	0.868	ns
DIFF_HSTL_I_18_F	0.319	0.319	0.339	0.319	0.339	0.456	0.456	0.474	0.456	0.474	0.576	0.576	0.606	0.576	0.606	ns
DIFF_HSTL_I_18_M	0.319	0.319	0.339	0.319	0.339	0.570	0.570	0.603	0.570	0.603	0.653	0.653	0.692	0.653	0.692	ns
DIFF_HSTL_I_18_S	0.319	0.319	0.339	0.319	0.339	0.782	0.782	0.834	0.782	0.834	0.816	0.816	0.871	0.816	0.871	ns
DIFF_HSTL_I_DCI_12_F	0.394	0.394	0.402	0.394	0.402	0.406	0.406	0.429	0.406	0.429	0.534	0.534	0.564	0.534	0.564	ns
DIFF_HSTL_I_DCI_12_M	0.394	0.394	0.402	0.394	0.402	0.557	0.557	0.587	0.557	0.587	0.653	0.653	0.694	0.653	0.694	ns
DIFF_HSTL_I_DCI_12_S	0.394	0.394	0.402	0.394	0.402	0.755	0.755	0.806	0.755	0.806	0.842	0.842	0.907	0.842	0.907	ns
DIFF_HSTL_I_DCI_18_F	0.323	0.323	0.339	0.323	0.339	0.445	0.445	0.461	0.445	0.461	0.566	0.566	0.595	0.566	0.595	ns
DIFF_HSTL_I_DCI_18_M	0.323	0.323	0.339	0.323	0.339	0.555	0.555	0.586	0.555	0.586	0.643	0.643	0.684	0.643	0.684	ns
DIFF_HSTL_I_DCI_18_S	0.323	0.323	0.339	0.323	0.339	0.762	0.762	0.818	0.762	0.818	0.836	0.836	0.900	0.836	0.900	ns
DIFF_HSTL_I_DCI_F	0.397	0.397	0.417	0.397	0.417	0.431	0.431	0.445	0.431	0.445	0.555	0.555	0.575	0.555	0.575	ns
DIFF_HSTL_I_DCI_M	0.397	0.397	0.417	0.397	0.417	0.553	0.553	0.583	0.553	0.583	0.644	0.644	0.684	0.644	0.684	ns
DIFF_HSTL_I_DCI_S	0.397	0.397	0.417	0.397	0.417	0.767	0.767	0.823	0.767	0.823	0.848	0.848	0.912	0.848	0.912	ns
DIFF_HSTL_I_F	0.404	0.404	0.417	0.404	0.417	0.423	0.423	0.443	0.423	0.443	0.549	0.549	0.581	0.549	0.581	ns
DIFF_HSTL_I_M	0.404	0.404	0.417	0.404	0.417	0.555	0.555	0.586	0.555	0.586	0.640	0.640	0.677	0.640	0.677	ns
DIFF_HSTL_I_S	0.404	0.404	0.417	0.404	0.417	0.767	0.767	0.818	0.767	0.818	0.811	0.811	0.866	0.811	0.866	ns
DIFF_HSUL_12_DCI_F	0.381	0.381	0.400	0.381	0.400	0.425	0.425	0.443	0.425	0.443	0.558	0.558	0.586	0.558	0.586	ns
DIFF_HSUL_12_DCI_M	0.381	0.381	0.400	0.381	0.400	0.557	0.557	0.587	0.557	0.587	0.653	0.653	0.694	0.653	0.694	ns
DIFF_HSUL_12_DCI_S	0.381	0.381	0.400	0.381	0.400	0.737	0.737	0.787	0.737	0.787	0.822	0.822	0.885	0.822	0.885	ns
DIFF_HSUL_12_F	0.394	0.394	0.402	0.394	0.402	0.412	0.412	0.430	0.412	0.430	0.538	0.538	0.566	0.538	0.566	ns
DIFF_HSUL_12_M	0.394	0.394	0.402	0.394	0.402	0.552	0.552	0.583	0.552	0.583	0.641	0.641	0.679	0.641	0.679	ns
DIFF_HSUL_12_S	0.394	0.394	0.402	0.394	0.402	0.752	0.752	0.800	0.752	0.800	0.813	0.813	0.868	0.813	0.868	ns
DIFF_POD10_DCI_F	0.411	0.411	0.430	0.411	0.430	0.425	0.425	0.444	0.425	0.444	0.555	0.555	0.584	0.555	0.584	ns
DIFF_POD10_DCI_M	0.411	0.411	0.430	0.411	0.430	0.542	0.542	0.571	0.542	0.571	0.640	0.640	0.681	0.640	0.681	ns
DIFF_POD10_DCI_S	0.411	0.411	0.430	0.411	0.430	0.754	0.754	0.815	0.754	0.815	0.850	0.850	0.917	0.850	0.917	ns
DIFF_POD10_F	0.411	0.411	0.433	0.411	0.433	0.438	0.438	0.459	0.438	0.459	0.569	0.569	0.601	0.569	0.601	ns
DIFF_POD10_M	0.411	0.411	0.433	0.411	0.433	0.538	0.538	0.568	0.538	0.568	0.630	0.630	0.667	0.630	0.667	ns
DIFF_POD10_S	0.411	0.411	0.433	0.411	0.433	0.766	0.766	0.821	0.766	0.821	0.836	0.836	0.894	0.836	0.894	ns
DIFF_POD12_DCI_F	0.407	0.407	0.432	0.407	0.432	0.425	0.425	0.443	0.425	0.443	0.558	0.558	0.586	0.558	0.586	ns
DIFF_POD12_DCI_M	0.407	0.407	0.432	0.407	0.432	0.543	0.543	0.572	0.543	0.572	0.638	0.638	0.678	0.638	0.678	ns
DIFF_POD12_DCI_S	0.407	0.407	0.432	0.407	0.432	0.772	0.772	0.822	0.772	0.822	0.862	0.862	0.929	0.862	0.929	ns
DIFF_POD12_F	0.409	0.409	0.430	0.409	0.430	0.455	0.455	0.476	0.455	0.476	0.595	0.595	0.626	0.595	0.626	ns
DIFF_POD12_M	0.409	0.409	0.430	0.409	0.430	0.551	0.551	0.582	0.551	0.582	0.641	0.641	0.679	0.641	0.679	ns
DIFF_POD12_S	0.409	0.409	0.430	0.409	0.430	0.767	0.767	0.817	0.767	0.817	0.832	0.832	0.889	0.832	0.889	ns
DIFF_SSTL12_DCI_F	0.381	0.381	0.400	0.381	0.400	0.425	0.425	0.443	0.425	0.443	0.558	0.558	0.586	0.558	0.586	ns
DIFF_SSTL12_DCI_M	0.381	0.381	0.400	0.381	0.400	0.557	0.557	0.587	0.557	0.587	0.654	0.654	0.694	0.654	0.694	ns
DIFF_SSTL12_DCI_S	0.381	0.381	0.400	0.381	0.400	0.754	0.754	0.803	0.754	0.803	0.842	0.842	0.908	0.842	0.908	ns

Block RAM and FIFO Switching Characteristics

Table 80: Block RAM and FIFO Switching Characteristics

Symbol	Description	Speed Grade and V _{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
Maximum Frequency							
F _{MAX_WF_NC}	Block RAM (WRITE_FIRST and NO_CHANGE modes).	825	738	645	585	516	MHz
F _{MAX_RF}	Block RAM (READ_FIRST mode).	718	637	575	510	460	MHz
F _{MAX_FIFO}	FIFO in all modes without ECC.	825	738	645	585	516	MHz
F _{MAX_ECC}	Block RAM and FIFO in ECC configuration without PIPELINE.	718	637	575	510	460	MHz
	Block RAM and FIFO in ECC configuration with PIPELINE and Block RAM in WRITE_FIRST or NO_CHANGE mode.	825	738	645	585	516	MHz
T _{PW} ⁽¹⁾	Minimum pulse width.	495	542	543	577	578	ps
Block RAM and FIFO Clock-to-Out Delays							
T _{RCKO_DO}	Clock CLK to DOUT output (without output register).	0.91	1.02	1.11	1.46	1.53	ns, Max
T _{RCKO_DO_REG}	Clock CLK to DOUT output (with output register).	0.27	0.29	0.30	0.42	0.44	ns, Max

Notes:

1. The MMCM and PLL DUTY_CYCLE attribute should be set to 50% to meet the pulse-width requirements at the higher frequencies.

Table 85: MMCM Specification (Cont'd)

Symbol	Description	Speed Grade and V _{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
MMCM_F _{DPRCLK_MAX}	Maximum DRP clock frequency	250	250	250	250	250	MHz

Notes:

1. The MMCM does not filter typical spread-spectrum input clocks because they are usually far below the bandwidth filter frequencies.
2. The static offset is measured between any MMCM outputs with identical phase.
3. Values for this parameter are available in the Clocking Wizard.
4. Includes global clock buffer.
5. Calculated as $F_{VCO}/128$ assuming output duty cycle is 50%.

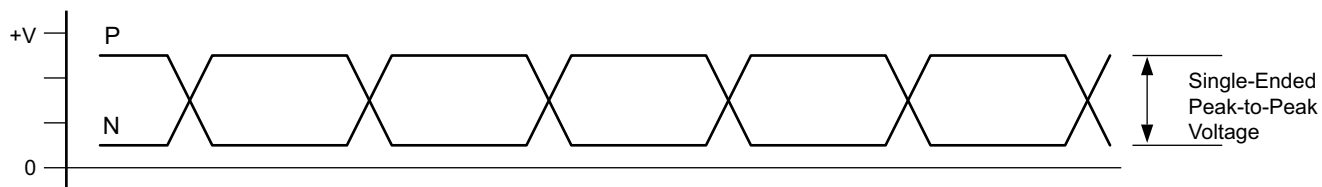
PLL Switching Characteristics

 Table 86: PLL Specification⁽¹⁾

Symbol	Description	Speed Grade and V _{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
PLL_F _{INMAX}	Maximum input clock frequency.	1066	933	800	933	800	MHz
PLL_F _{INMIN}	Minimum input clock frequency.	70	70	70	70	70	MHz
PLL_F _{INJITTER}	Maximum input clock period jitter.	< 20% of clock input period or 1 ns Max					
PLL_F _{INDUTY}	Input duty cycle range: 70–399 MHz.	35–65					%
	Input duty cycle range: 400–499 MHz.	40–60					%
	Input duty cycle range: >500 MHz.	45–55					%
PLL_F _{VCOMIN}	Minimum PLL VCO frequency.	750	750	750	750	750	MHz
PLL_F _{VCOMAX}	Maximum PLL VCO frequency.	1500	1500	1500	1500	1500	MHz
PLL_T _{STATPHAOFFSET}	Static phase offset of the PLL outputs. ⁽²⁾	0.12	0.12	0.12	0.12	0.12	ns
PLL_T _{OUTJITTER}	PLL output jitter.	Note 3					
PLL_T _{OUTDUTY}	PLL CLKOUT0, CLKOUT0B, CLKOUT1, CLKOUT1B duty-cycle precision. ⁽⁴⁾	0.165	0.20	0.20	0.20	0.20	ns
PLL_T _{LOCKMAX}	PLL maximum lock time.	100					µs
PLL_F _{OUTMAX}	PLL maximum output frequency at CLKOUT0, CLKOUT0B, CLKOUT1, CLKOUT1B.	891	775	667	725	667	MHz
	PLL maximum output frequency at CLKOUTPHY.	2667	2667	2400	2400	2133	MHz
PLL_F _{OUTMIN}	PLL minimum output frequency at CLKOUT0, CLKOUT0B, CLKOUT1, CLKOUT1B. ⁽⁵⁾	5.86	5.86	5.86	5.86	5.86	MHz
	PLL minimum output frequency at CLKOUTPHY.	2 x VCO mode: 1500, 1 x VCO mode: 750 0.5 x VCO mode: 375					MHz
PLL_RST _{MINPULSE}	Minimum reset pulse width.	5.00	5.00	5.00	5.00	5.00	ns
PLL_F _{PFDMAX}	Maximum frequency at the phase frequency detector.	667.5	667.5	667.5	667.5	667.5	MHz
PLL_F _{PFDMIN}	Minimum frequency at the phase frequency detector.	70	70	70	70	70	MHz
PLL_F _{BANDWIDTH}	PLL bandwidth at typical.	14	14	14	14	14	MHz
PLL_F _{DPRCLK_MAX}	Maximum DRP clock frequency	250	250	250	250	250	MHz

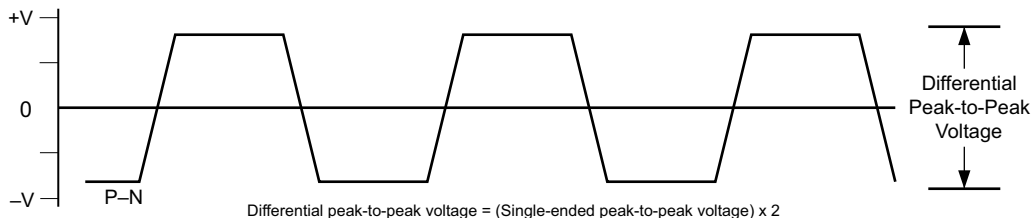
Notes:

1. The PLL does not filter typical spread-spectrum input clocks because they are usually far below the loop filter frequencies.
2. The static offset is measured between any PLL outputs with identical phase.
3. Values for this parameter are available in the Clocking Wizard.
4. Includes global clock buffer.
5. Calculated as F_{VCO}/128 assuming output duty cycle is 50%.



X16653-101316

Figure 3: Single-Ended Peak-to-Peak Voltage



X16639-101316

Figure 4: Differential Peak-to-Peak Voltage

Table 95 and Table 96 summarize the DC specifications of the GTH transceivers input and output clocks in Zynq UltraScale+ MPSoC. Consult the *UltraScale Architecture GTH Transceiver User Guide (UG576)* for further details.

Table 95: GTH Transceiver Clock Input Level Specification

Symbol	DC Parameter	Min	Typ	Max	Units
V_{IDIFF}	Differential peak-to-peak input voltage.	250	–	2000	mV
R_{IN}	Differential input resistance.	–	100	–	Ω
C_{EXT}	Required external AC coupling capacitor.	–	10	–	nF

Table 96: GTH Transceiver Clock Output Level Specification

Symbol	Description	Conditions	Min	Typ	Max	Units
V_{OL}	Output Low voltage for P and N.	$R_T = 100\Omega$ across P and N signals	100	–	330	mV
V_{OH}	Output High voltage for P and N.	$R_T = 100\Omega$ across P and N signals	500	–	700	mV
V_{DDOUT}	Differential output voltage. (P–N), P = High (N–P), N = High	$R_T = 100\Omega$ across P and N signals	300	–	430	mV
V_{CMOUT}	Common mode voltage.	$R_T = 100\Omega$ across P and N signals	300	–	500	mV

Table 103: GTH Transceiver Transmitter Switching Characteristics (Cont'd)

Symbol	Description	Condition	Min	Typ	Max	Units
T _{J2.5}	Total jitter ⁽³⁾⁽⁴⁾	2.5 Gb/s ⁽⁶⁾	–	–	0.20	UI
D _{J2.5}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.10	UI
T _{J1.25}	Total jitter ⁽³⁾⁽⁴⁾	1.25 Gb/s ⁽⁷⁾	–	–	0.15	UI
D _{J1.25}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.06	UI
T _{J500}	Total jitter ⁽³⁾⁽⁴⁾	500 Mb/s ⁽⁸⁾	–	–	0.10	UI
D _{J500}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.03	UI

Notes:

- Using same REFCLK input with TX phase alignment enabled for up to four consecutive transmitters (one fully populated GTH Quad) at the maximum line rate.
- Using QPLL_FBDIV = 40, 20-bit internal data width. These values are NOT intended for protocol specific compliance determinations.
- Using CPLL_FBDIV = 2, 20-bit internal data width. These values are NOT intended for protocol specific compliance determinations.
- All jitter values are based on a bit-error ratio of 10⁻¹².
- CPLL frequency at 3.2 GHz and TXOUT_DIV = 2.
- CPLL frequency at 2.5 GHz and TXOUT_DIV = 2.
- CPLL frequency at 2.5 GHz and TXOUT_DIV = 4.
- CPLL frequency at 2.0 GHz and TXOUT_DIV = 8.

Table 104: GTH Transceiver Receiver Switching Characteristics

Symbol	Description	Condition	Min	Typ	Max	Units
F _{GTHRX}	Serial data rate		0.500	–	F _{GTHMAX}	Gb/s
R _{XSSST}	Receiver spread-spectrum tracking ⁽¹⁾	Modulated at 33 kHz	–5000	–	0	ppm
R _{XRL}	Run length (CID)		–	–	256	UI
R _{XPPMTOL}	Data/REFCLK PPM offset tolerance	Bit rates ≤ 6.6 Gb/s	–1250	–	1250	ppm
		Bit rates > 6.6 Gb/s and ≤ 8.0 Gb/s	–700	–	700	ppm
		Bit rates > 8.0 Gb/s	–200	–	200	ppm
SJ Jitter Tolerance⁽²⁾						
J _{T_SJ16.375}	Sinusoidal jitter (QPLL) ⁽³⁾	16.375 Gb/s	0.30	–	–	UI
J _{T_SJ15.0}	Sinusoidal jitter (QPLL) ⁽³⁾	15.0 Gb/s	0.30	–	–	UI
J _{T_SJ14.1}	Sinusoidal jitter (QPLL) ⁽³⁾	14.1 Gb/s	0.30	–	–	UI
J _{T_SJ13.1}	Sinusoidal jitter (QPLL) ⁽³⁾	13.1 Gb/s	0.30	–	–	UI
J _{T_SJ12.5}	Sinusoidal jitter (QPLL) ⁽³⁾	12.5 Gb/s	0.30	–	–	UI
J _{T_SJ11.3}	Sinusoidal jitter (QPLL) ⁽³⁾	11.3 Gb/s	0.30	–	–	UI
J _{T_SJ10.32_QPLL}	Sinusoidal jitter (QPLL) ⁽³⁾	10.32 Gb/s	0.30	–	–	UI
J _{T_SJ10.32_CPLL}	Sinusoidal jitter (CPLL) ⁽³⁾	10.32 Gb/s	0.30	–	–	UI
J _{T_SJ9.953_QPLL}	Sinusoidal jitter (QPLL) ⁽³⁾	9.953 Gb/s	0.30	–	–	UI
J _{T_SJ9.953_CPLL}	Sinusoidal jitter (CPLL) ⁽³⁾	9.953 Gb/s	0.30	–	–	UI
J _{T_SJ8.0}	Sinusoidal jitter (QPLL) ⁽³⁾	8.0 Gb/s	0.42	–	–	UI
J _{T_SJ6.6_CPLL}	Sinusoidal jitter (CPLL) ⁽³⁾	6.6 Gb/s	0.44	–	–	UI
J _{T_SJ5.0}	Sinusoidal jitter (CPLL) ⁽³⁾	5.0 Gb/s	0.44	–	–	UI
J _{T_SJ4.25}	Sinusoidal jitter (CPLL) ⁽³⁾	4.25 Gb/s	0.44	–	–	UI
J _{T_SJ3.2}	Sinusoidal jitter (CPLL) ⁽³⁾	3.2 Gb/s ⁽⁴⁾	0.45	–	–	UI

Table 114: GTY Transceiver User Clock Switching Characteristics⁽¹⁾ (Cont'd)

Symbol	Description	Data Width Conditions (Bit)		Speed Grade and V _{CCINT} Operating Voltages					Units
				0.90V		0.85V		0.72V	
		Internal Logic	Interconnect Logic	-3 ⁽²⁾	-2 ⁽²⁾⁽³⁾	-1 ⁽⁴⁾⁽⁵⁾	-2 ⁽³⁾	-1 ⁽⁵⁾	
F _{TXIN2}	TXUSRCLK2 ⁽⁶⁾ maximum frequency	16	16	511.719	511.719	390.625	390.625	322.266	MHz
		16	32	255.859	255.859	195.313	195.313	161.133	MHz
		32	32	511.719	511.719	390.625	390.625	322.266	MHz
		32	64	255.859	255.859	195.313	195.313	161.133	MHz
		64	64	511.719	440.781	402.832	402.832	195.313	MHz
		64	128	255.859	220.391	201.416	201.416	97.656	MHz
		20	20	409.375	409.375	312.500	312.500	257.813	MHz
		20	40	204.688	204.688	156.250	156.250	128.906	MHz
		40	40	409.375	409.375	312.500	350.000	257.813	MHz
		40	80	204.688	204.688	156.250	175.000	128.906	MHz
		80	80	409.375	352.625	322.266	352.625	156.250	MHz
80	160	204.688	176.313	161.133	176.313	78.125	MHz		
F _{RXIN2}	RXUSRCLK2 ⁽⁶⁾ maximum frequency	16	16	511.719	511.719	390.625	390.625	322.266	MHz
		16	32	255.859	255.859	195.313	195.313	161.133	MHz
		32	32	511.719	511.719	390.625	390.625	322.266	MHz
		32	64	255.859	255.859	195.313	195.313	161.133	MHz
		64	64	511.719	440.781	402.832	402.832	195.313	MHz
		64	128	255.859	220.391	201.416	201.416	97.656	MHz
		20	20	409.375	409.375	312.500	312.500	257.813	MHz
		20	40	204.688	204.688	156.250	156.250	128.906	MHz
		40	40	409.375	409.375	312.500	350.000	257.813	MHz
		40	80	204.688	204.688	156.250	175.000	128.906	MHz
		80	80	409.375	352.625	322.266	352.625	156.250	MHz
80	160	204.688	176.313	161.133	176.313	78.125	MHz		

Notes:

1. Clocking must be implemented as described in the *UltraScale Architecture GTY Transceiver User Guide* ([UG578](#)).
2. For speed grades -3E, -2E, and -2I, a 16-bit and 20-bit internal data path can only be used for line rates less than 8.1875 Gb/s.
3. For speed grade -2LE, a 16-bit and 20-bit internal data path can only be used for line rates less than 8.1875 Gb/s when V_{CCINT} = 0.85V or 6.25 Gb/s when V_{CCINT} = 0.72V.
4. For speed grades -1E and -1I, a 16-bit and 20-bit internal data path can only be used for line rates less than 6.25 Gb/s.
5. For speed grade -1LI, a 16-bit and 20-bit internal data path can only be used for line rates less than 6.25 Gb/s when V_{CCINT} = 0.85V or 5.15625 Gb/s when V_{CCINT} = 0.72V.
6. When the gearbox is used, these maximums refer to the XCLK. For more information, see the *Valid Data Width Combinations for TX Asynchronous Gearbox* table in the *UltraScale Architecture GTY Transceiver User Guide* ([UG578](#)).

PL SYSMON I2C/PMBus Interfaces

Table 125: PL SYSMON I2C Fast Mode Interface Switching Characteristics⁽¹⁾

Symbol	Description	Min	Max	Units
T_{SMFCKL}	SCL Low time	1.3	–	μ s
T_{SMFCKH}	SCL High time	0.6	–	μ s
T_{SMFCKO}	SDAO clock-to-out delay	–	900	ns
T_{SMFDCK}	SDAI setup time	100	–	ns
F_{SMFCLK}	SCL clock frequency	–	400	kHz

Notes:

1. The test conditions are configured to the LVCMOS 1.8V I/O standard.

Table 126: PL SYSMON I2C Standard Mode Interface Switching Characteristics⁽¹⁾

Symbol	Description	Min	Max	Units
T_{SMSCKL}	SCL Low time	4.7	–	μ s
T_{SMSCKH}	SCL High time	4.0	–	μ s
T_{SMSCKO}	SDAO clock-to-out delay	–	3450	ns
T_{SMSDCK}	SDAI setup time	250	–	ns
F_{SMSCLK}	SCL clock frequency	–	100	kHz

Notes:

1. The test conditions are configured to the LVCMOS 1.8V I/O standard.

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